



SiC

| Type No. | Housing | Radiant Sensitivity mAW | Sensitive Area mm ² | Dark Current nA U _i =1V | Capacitance Ct [pF] 0V, f=1MHz | Spectral sensitivity λ [nm] | Peak wavelength λ _p [nm] | Half angle Δθ [deg] |
|-------------|---------|----------------------------|-----------------------------------|--|--------------------------------------|--------------------------------|--|------------------------|
| SiC0.25TF-3 | TO46 | 130 | 0.25 | 0.04 | 27 | 180~370 | 275 | 30 |
| SiC1.0TF-3 | TO46 | 130 | 1 | 0.1 | 97 | 180~370 | 275 | 30 |
| SiC9.0TF-3 | TO5 | 130 | 9 | 0.4 | 440 | 180~370 | 275 | 30 |

UV Photodiodes

| Type No. | Housing | Radiant Sensitivity mAW | Sensitive Area mm ² | Dark Current nA U _i =1V | Capacitance Ct [pF] 0V, f=1MHz | Spectral sensitivity λ [nm] | Peak wavelength λ _p [nm] | Half angle Δθ [deg] |
|-------------|---------|----------------------------|-----------------------------------|--|--------------------------------------|--------------------------------|--|------------------------|
| SiC0.25TF-3 | TO46 | 130 | 0.25 | 0.04 | 27 | 180~370 | 275 | 30 |
| SiC1.0TF-3 | TO46 | 130 | 1 | 0.1 | 97 | 180~370 | 275 | 30 |
| SiC9.0TF-3 | TO5 | 130 | 9 | 0.4 | 440 | 180~370 | 275 | 30 |

PN TYPE

Survey

| Type No. | Housing | Gain | Sensitive Area um (dia.) | Responsivity nw/cm ² | Breakdown Voltage V | Quantum Efficiency | Dark current pA | Dark count range KHz |
|------------|---------|----------|-----------------------------|------------------------------------|------------------------|--------------------|--------------------|-------------------------|
| APD1.0TF-3 | TO46 | 1.00E+06 | 120 | 1 | 165~180 | 35% | 1.5 | 10 |

APD TYPE